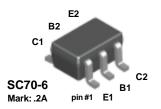


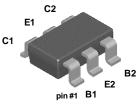
FFB3906

FMB3906

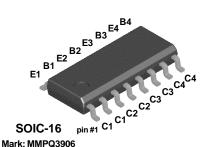
MMPQ3906



NOTE: The pinouts are symmetrical; pin 1 and pin 4 are interchangeable. Units inside the carrier can be of either orientation and will not affect the functionality of the device.







PNP Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at collector currents of 10 µA to 100 mA. Sourced from Process 66.

Absolute Maximum Ratings*

 $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

T_a = 25°C unless otherwise noted

Symbol	Characteristic Max		Max		Units	
		FFB3904	FMB3904	MMPQ3904		
P_D	Total Device Dissipation Derate above 25°C	300 2.4	700 5.6	1,000 8.0	mW mW/°C	
R ₀ JA	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	415	180	125 240	°C/W °C/W	

(continued)

El	ectr	ica	l CI	har	act	er	isti	ics

T_A = 25°C unless otherwise noted

OFF CHARACTE	RISTICS				
V _{(BR)CEO} Collective Voltage	ctor-Emitter Breakdown ge*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO} Collect	ctor-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, \ I_E = 0$	40		V
V _{(BR)EBO} Emitte	er-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{BL} Base	Cutoff Current	V _{CE} = 30 V, V _{BE} = 3.0 V		50	nA
I _{CEX} Collect	ctor Cutoff Current	V _{CE} = 30 V, V _{BE} = 3.0 V		50	nA

h _{FE}	DC Current Gain *	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60		
		$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	80		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100	300	
		$I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60		
		$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	30		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.25	V
, ,	_	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.65	0.85	V
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.95	V

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	450	MHz
C _{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ f = 100 kHz	3.0	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0,$ f = 100 kHz	8.0	pF
NF	Noise Figure (except MMPQ3906)	$I_C = 100 \mu A, V_{CE} = 5.0 V,$	2.5	dB
		$R_S = 1.0 k\Omega$, $f=10$ Hz to 15.7 kHz		

SWITCHING CHARACTERISTICS

t _d	Delay Time	$V_{CC} = 3.0 \text{ V}, V_{BE} = 0.5 \text{ V},$	15	ns
t _r	Rise Time	$I_C = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA}$	20	ns
ts	Storage Time	V _{CC} = 3.0 V, I _C = 10mA	110	ns
t _f	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$	40	ns

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Spice Model

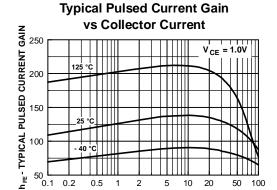
PNP (Is=1.41f Xti=3 Eg=1.11 Vaf=18.7 Bf=180.7 Ne=1.5 Ise=0 Ikf=80m Xtb=1.5 Br=4.977 Nc=2 Isc=0 Ikr=0 Rc=2.5 Cjc=9.728p Mjc=.5776 Vjc=.75 Fc=.5 Cje=8.063p Mje=.3677 Vje=.75 Tr=33.42n Tf=179.3p Itf=.4 Vtf=4 Xtf=6 Rb=10)

(continued)

Typical Characteristics

0.5

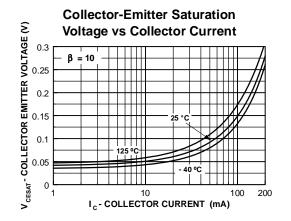
50 L 0.1 0.2

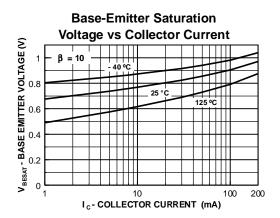


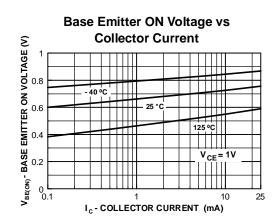
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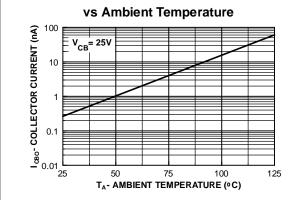
I_c - COLLECTOR CURRENT (mA)

5 10 20 50

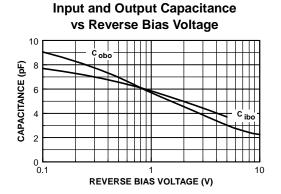








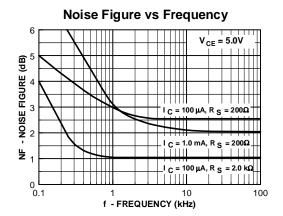
Collector-Cutoff Current

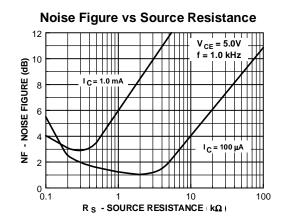


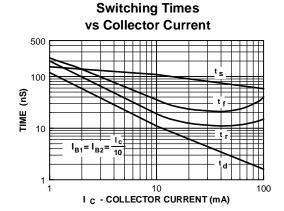
Common-Base Open Circuit

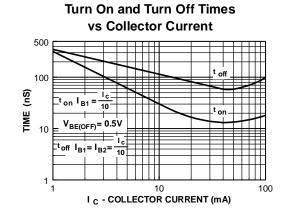
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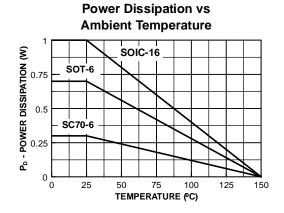
Typical Characteristics (continued)





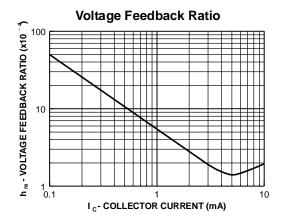


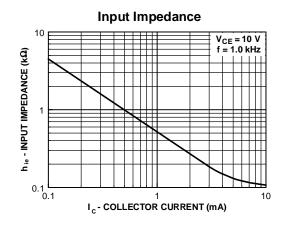


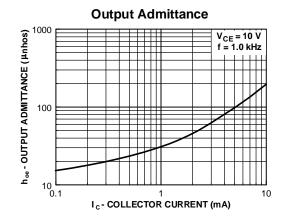


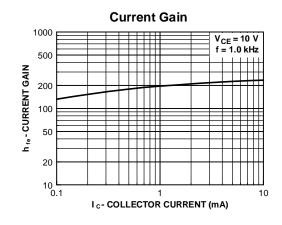
(continued)

Typical Characteristics (continued)









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